

# Dae-Kue Hwang

## List of Publications by Year in descending order

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103  
papers

4,818  
citations

182225  
30  
h-index

107981  
68  
g-index

103  
all docs

103  
docs citations

103  
times ranked

5675  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of Metal-Precursor Stacking Order on Volume-Defect Formation in CZTSSe Thin Film: Formation Mechanism of Blisters and Nanopores. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 30649-30657.	4.0	4
2	Atomic Layer Deposition of Ultrathin ZnO Films for Hybrid Window Layers for Cu(In <sub>x</sub> Ga <sub>1-x</sub> )Se <sub>2</sub> Solar Cells. <i>Nanomaterials</i> , 2021, 11, 2779.	1.9	10
3	Effects of the annealing temperature on the properties of sulfur-graded Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> thin films grown by a modified two-step process. <i>Journal of Industrial and Engineering Chemistry</i> , 2020, 82, 406-412.	2.9	5
4	Induced Growth of CsPbBr <sub>3</sub> Perovskite Films by Incorporating Metal Chalcogenide Quantum Dots in PbBr <sub>2</sub> Films for Performance Enhancement of Inorganic Perovskite Solar Cells. <i>ACS Applied Energy Materials</i> , 2020, 3, 10376-10383.	2.5	21
5	Effect of embedded chalcogenide quantum dots in PbBr <sub>2</sub> film on CsPbBr <sub>3</sub> inorganic perovskite solar cells. <i>Journal of Industrial and Engineering Chemistry</i> , 2020, 90, 281-286.	2.9	10
6	Improvement of Ga distribution with Sb incorporation for two-step low-temperature processing of CIGSe thin film solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2019, 194, 244-251.	3.0	6
7	Void and secondary phase formation mechanisms of CZTSSe using Sn/Cu/Zn/Mo stacked elemental precursors. <i>Nano Energy</i> , 2019, 59, 399-411.	8.2	61
8	Effect of solid-H <sub>2</sub> S gas reactions on CZTSSe thin film growth and photovoltaic properties of a 12.62% efficiency device. <i>Journal of Materials Chemistry A</i> , 2019, 7, 25279-25289.	5.2	229
9	Efficiency enhancement of bifacial Cu <sub>2</sub> ZnSnSe <sub>4</sub> thin-film solar cells on indium tin oxide glass substrates by suppressing In-Sn diffusion with Mo interlayer. <i>Journal of Power Sources</i> , 2018, 400, 9-15.	4.0	11
10	Fabrication of Sb <sub>2</sub> S <sub>3</sub> Hybrid Solar Cells Based on Embedded Photoelectrodes of Ag Nanowires-Au Nanoparticles Composite. <i>Journal of Nanoscience and Nanotechnology</i> , 2018, 18, 6520-6523.	0.9	2
11	Single-step sulfo-selenization method for achieving low open circuit voltage deficit with band gap front-graded Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> thin films. <i>Solar Energy Materials and Solar Cells</i> , 2017, 161, 162-169.	3.0	55
12	Mesoporous TiO <sub>2</sub> hierarchical structures: preparation and efficacy in solar cells. <i>RSC Advances</i> , 2017, 7, 49057-49065.	1.7	8
13	Quasi-solid state electrolyte for semi-transparent bifacial dye-sensitized solar cell with over 10% power conversion efficiency. <i>Journal of Power Sources</i> , 2017, 361, 87-95.	4.0	31
14	Comparison of chalcopyrite and kesterite thin-film solar cells. <i>Journal of Industrial and Engineering Chemistry</i> , 2017, 45, 78-84.	2.9	23
15	Effect of Ag Nanowire/ZnO Core-Shell Photoelectrodes in Sb <sub>2</sub> S <sub>3</sub> -Based Hybrid Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 8201-8204.	0.9	1
16	Optimization of Electrolyte Components on the Performance of Organic-Dye-Sensitized Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 8100-8104.	0.9	1
17	Enhanced Performance of Dye-Sensitized Solar Cells Based on Electrospun TiO <sub>2</sub> Electrode. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 8117-8121.	0.9	1
18	Control of Zn Content and Influence on Cu <sub>2</sub> ZnSnSe <sub>4</sub> Thin-Film Solar Cells Fabricated by Coevaporation. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 8236-8241.	0.9	2

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19	Effects of Back Annealing on the Structural and Electrical Properties of Cu <sub>2</sub> ZnSnSe <sub>4</sub> Thin Films Grown by a Modified Two-Step Process. <i>Science of Advanced Materials</i> , 2017, 10, 580-585.	0.1	1
20	In Situ Synthesis of Gold Nanoparticles in Poly(3,4-ethylenedioxythiophene): Poly(styrenesulfonate) and Application to Hybrid Solar Cells. <i>Science of Advanced Materials</i> , 2017, 10, 560-564.	0.1	3
21	High efficiency bifacial Cu <sub>2</sub> ZnSnSe <sub>4</sub> thin-film solar cells on transparent conducting oxide glass substrates. <i>APL Materials</i> , 2016, 4, .	2.2	40
22	Optimization of the ZnS Buffer Layer by Chemical Bath Deposition for Cu(In,Ga)Se <sub>2</sub> Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 5398-5402.	0.9	11
23	A band-gap-graded CZTSSe solar cell with 12.3% efficiency. <i>Journal of Materials Chemistry A</i> , 2016, 4, 10151-10158.	5.2	260
24	Effect of Perovskite Overlayers on TiO <sub>2</sub> Electrodes in Perovskite-Sensitized Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 5305-5307.	0.9	0
25	Fabrication of Dye-Sensitized Solar Cells Based on Embedded Photoelectrodes of TiO <sub>2</sub> Nanotube-Nanoparticles Composite. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 10716-10719.	0.9	0
26	Controlled fabrication of mesoporous TiO <sub>2</sub> hierarchical structures as scattering layers to enhance the power conversion efficiency of dye-sensitized solar cells. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 30254-30260.	1.3	2
27	Effect of Thickness of Electrospayed TiO <sub>2</sub> Photoelectrode for Application in Transparent Yellow Color Dye-Sensitized Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 10597-10601.	0.9	1
28	Effect of Structural Non-Planarity and $\pi$ -Conjugated Unit of Novel Bicarbazole Derivatives for Dye-Sensitized Solar Cells. <i>Science of Advanced Materials</i> , 2016, 8, 1381-1389.	0.1	1
29	Effects of Thickness of Electrospayed Spherical TiO <sub>2</sub> Photoelectrodes on the Performance of Dye-Sensitized Solar Cells. <i>Science of Advanced Materials</i> , 2016, 8, 640-644.	0.1	0
30	Effects of a Pretreatment on Al-Doped ZnO Thin Films Grown by Atomic Layer Deposition. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 2432-2435.	0.9	4
31	Nanostructured p-type CZTS thin films prepared by a facile solution process for 3D $\mu$ n junction solar cells. <i>Nanoscale</i> , 2015, 7, 11182-11189.	2.8	27
32	Characterization of in-situ annealed sub-micron thick Cu(In,Ga)Se <sub>2</sub> thin films. <i>Thin Solid Films</i> , 2015, 590, 330-334.	0.8	4
33	Fabrication of High Efficiency Dye-Sensitized Solar Cells Based on TiO <sub>2</sub> Nanoparticles Embedded in Ti Substrate. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 241-243.	0.9	1
34	Electrospun ZnO Nanofibers as a Photoelectrode in Dye-Sensitized Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 2346-2350.	0.9	10
35	Effect of TiCl <sub>4</sub> Post-Treatment on the Embedded-Type TiO <sub>2</sub> Nanotubes Dye-Sensitized Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 7845-7847.	0.9	1
36	Effects of Na and MoS <sub>2</sub> on Cu <sub>2</sub> ZnSnS <sub>4</sub> thin-film solar cell. <i>Progress in Photovoltaics: Research and Applications</i> , 2015, 23, 862-873.	4.4	108



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55	Effect of TiO <sub>2</sub> Nanoparticle Modification on Ultraviolet Photodetection Properties of Al-Doped ZnO Nanowire Network. Japanese Journal of Applied Physics, 2011, 50, 06GF07.	0.8	3
56	Effect of VI/II Gas Ratio on the Epitaxial Growth of ZnO Films by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2011, 50, 105502.	0.8	6
57	Materials, Interfaces, and Photon Confinement in Dye-Sensitized Solar Cells. Journal of Physical Chemistry B, 2010, 114, 14582-14591.	1.2	76
58	Recent Advances in ZnO-Based Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2010, 57, 26-41.	1.6	333
59	Formation of Macropore and Three-Dimensional Nanorod Array in p-Type Silicon. Japanese Journal of Applied Physics, 2010, 49, 056503.	0.8	4
60	Work Function Modification of Indium-Tin Oxide by Surface Plasma Treatments Using Different Gases. Japanese Journal of Applied Physics, 2009, 48, 021601.	0.8	27
61	Photonic bandgap engineering with inverse opal multistacks of different refractive index contrasts. Applied Physics Letters, 2009, 95, 091101.	1.5	31
62	Effects of surface roughness on the electrical characteristics of ZnO nanowire field effect transistors. Applied Surface Science, 2008, 254, 7559-7564.	3.1	28
63	Fabrication and characterizations of ZnO thin film transistors prepared by using radio frequency magnetron sputtering. Solid-State Electronics, 2008, 52, 813-816.	0.8	49
64	Impact of Hydrogenation of ZnO TFTs by Plasma-Deposited Silicon Nitride Gate Dielectric. IEEE Transactions on Electron Devices, 2008, 55, 2736-2743.	1.6	20
65	Tunable Electronic Transport Characteristics of Surface-Architecture-Controlled ZnO Nanowire Field Effect Transistors. Nano Letters, 2008, 8, 950-956.	4.5	235
66	Effect of pressure on the properties of phosphorus-doped p-type ZnO thin films grown by radio frequency-magnetron sputtering. Applied Physics Letters, 2008, 92, .	1.5	32
67	Growth and Characterization of Gallium-Doped ZnO Films for $\beta$ -Particle Scintillators. Journal of the Electrochemical Society, 2008, 155, H909.	1.3	10
68	Effect of N <sub>2</sub> O Plasma Treatment on the Performance of ZnO TFTs. Electrochemical and Solid-State Letters, 2008, 11, H55.	2.2	62
69	Improvement of Characteristics of Ga-Doped ZnO Grown by Pulsed Laser Deposition Using Plasma-Enhanced Oxygen Radicals. Journal of the Electrochemical Society, 2008, 155, D599.	1.3	29
70	Effect of Rapid Thermal Annealing on the Electrical Characteristics of ZnO Thin-Film Transistors. Japanese Journal of Applied Physics, 2008, 47, 2848-2853.	0.8	25
71	Improving the Gate Stability of ZnO Thin-Film Transistors with Aluminum Oxide Dielectric Layers. Journal of the Electrochemical Society, 2008, 155, H1009.	1.3	45
72	Microstructural properties of phosphorus-doped p-type ZnO grown by radio-frequency magnetron sputtering. Applied Physics Letters, 2008, 93, .	1.5	35

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73	Current-driven hydrogen incorporation in zinc oxide. Applied Physics Letters, 2007, 91, 212102.	1.5	26
74	ZnO-based light-emitting metal-insulator-semiconductor diodes. Applied Physics Letters, 2007, 91, .	1.5	50
75	Effect of annealing temperature and ambient gas on phosphorus doped p-type ZnO. Applied Physics Letters, 2007, 90, 021106.	1.5	58
76	ZnO thin films and light-emitting diodes. Journal Physics D: Applied Physics, 2007, 40, R387-R412.	1.3	187
77	Improvement of Pt Schottky contacts to n-type ZnO by KrF excimer laser irradiation. Applied Physics Letters, 2007, 91, .	1.5	43
78	ZnO-based thin film transistors having high refractive index silicon nitride gate. Applied Physics Letters, 2007, 91, 182101.	1.5	24
79	Realization of highly reproducible ZnO nanowire field effect transistors with n-channel depletion and enhancement modes. Applied Physics Letters, 2007, 90, 243103.	1.5	52
80	Optical investigation of p-type ZnO epilayers doped with different phosphorus concentrations by radio-frequency magnetron sputtering. Applied Physics Letters, 2007, 91, 061903.	1.5	33
81	Deformation behavior during nanoindentation of epitaxial ZnO thin films on sapphire substrate. Materials Letters, 2007, 61, 2443-2445.	1.3	7
82	A nanoindentation study of the mechanical properties of ZnO thin films on (0 0 0 1) sapphire. Applied Surface Science, 2006, 253, 464-467.	3.1	37
83	UV Electroluminescence Emission from ZnO Light-Emitting Diodes Grown by High-Temperature Radiofrequency Sputtering. Advanced Materials, 2006, 18, 2720-2724.	11.1	592
84	Effects of Electrical Bias Stress on the Performance of ZnO-Based TFTs Fabricated by RF Magnetron Sputtering. Journal of the Electrochemical Society, 2006, 153, G385.	1.3	60
85	Low resistance nonalloyed Ni <sup>2+</sup> /Au Ohmic contacts to p-GaN irradiated by KrF excimer laser. Applied Physics Letters, 2006, 89, 042107.	1.5	14
86	The Effect of Ar <sup>2+</sup> Sputtering Gas on the Phosphorus-Doped p-Type ZnO Thin Films. Journal of the Electrochemical Society, 2006, 153, G242.	1.3	17
87	Highly transparent ZnO spreading layer for GaN based LED. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2533-2535.	0.8	3
88	Zn <sup>2+</sup> /Au Ohmic Contacts on n-Type ZnO Epitaxial Layers for Light-Emitting Devices. Electrochemical and Solid-State Letters, 2005, 8, G198.	2.2	21
89	Low-resistance and highly transparent Ni/indium-tin oxide ohmic contacts to phosphorous-doped p-type ZnO. Applied Physics Letters, 2005, 86, 211902.	1.5	24
90	Formation of Low Resistance Nonalloyed Ti <sup>2+</sup> /Au Ohmic Contacts to n-Type ZnO by KrF Excimer Laser Irradiation. Electrochemical and Solid-State Letters, 2005, 8, G317.	2.2	16

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91	Formation and Effect of Thermal Annealing for Low-Resistance Ni/Au Ohmic Contact to Phosphorous-Doped p-Type ZnO. Journal of the Electrochemical Society, 2005, 152, G179.	1.3	34
92	Highly transparent and low resistance gallium-doped indium oxide contact to p-type GaN. Applied Physics Letters, 2005, 87, 042109.	1.5	20
93	High-performance GaN-based light-emitting diode using high-transparency Ni <sup>2+</sup> •Au <sup>3+</sup> •Al-doped ZnO composite contacts. Applied Physics Letters, 2005, 87, 181107.	1.5	29
94	Effect of Interlayers on the Indium Oxide-Doped ZnO Ohmic Contact to p-Type GaN. Journal of the Electrochemical Society, 2005, 152, G491.	1.3	10
95	Study of the photoluminescence of phosphorus-doped p-type ZnO thin films grown by radio-frequency magnetron sputtering. Applied Physics Letters, 2005, 86, 151917.	1.5	230
96	p-ZnO/n-GaN heterostructure ZnO light-emitting diodes. Applied Physics Letters, 2005, 86, 222101.	1.5	337
97	Low-resistivity and transparent indium-oxide-doped ZnO ohmic contact to p-type GaN. Applied Physics Letters, 2004, 85, 6191-6193.	1.5	64
98	Growth of Buffer-Free High-Quality ZnO Epilayer on Sapphire (0001) Using Radio-Frequency Magnetron Sputtering. Journal of the Electrochemical Society, 2004, 151, G623.	1.3	16
99	Growth of Buffer-Free High-Quality ZnO Epilayer on Sapphire (0001) Using Radio-Frequency Magnetron Sputtering [J. Electrochem. Soc., 151, G623 (2004)]. Journal of the Electrochemical Society, 2004, 151, L15.	1.3	0
100	Realization of p-type ZnO thin films via phosphorus doping and thermal activation of the dopant. Applied Physics Letters, 2003, 83, 63-65.	1.5	600
101	Effects of As Doping on Properties of ZnO Films. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	1
102	Electrical and optical properties of silicon quantum dots light-emitting diode by using highly doped ZnO. , 0, , .		0
103	Resistance switching of Al doped ZnO for Non Volatile Memory applications. , 0, , .		2